

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property
Organization
International Bureau

(43) International Publication Date
07 May 2020 (07.05.2020)



(10) International Publication Number
WO 2020/091961 A1

- (51) **International Patent Classification:**
H01L 21/768 (2006.01) *H01L 21/3205* (2006.01)
H01L 21/02 (2006.01)
- (21) **International Application Number:**
PCT/US2019/055210
- (22) **International Filing Date:**
08 October 2019 (08.10.2019)
- (25) **Filing Language:** English
- (26) **Publication Language:** English
- (30) **Priority Data:**
62/752,334 29 October 2018 (29.10.2018) US
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(81) **Designated States** (*unless otherwise indicated, for every
kind of national protection available*): AE, AG, AL, AM,
AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ,
CA, CH, CL, CN, CO, CR, CU, CZ, DE, DJ, DK, DM, DO,
DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN,
HR, HU, ID, IL, IN, IR, IS, JO, JP, KE, KG, KH, KN, KP,
KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, ME,
MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ,
OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SA,
SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN,
TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) **Designated States** (*unless otherwise indicated, for every
kind of regional protection available*): ARIPO (BW, GH,
GM, KE, LR, LS, MW, MZ, NA, RW, SD, SL, ST, SZ, TZ,
UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ,
TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK,
EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV,
MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM,
TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW,
KM, ML, MR, NE, SN, TD, TG).

(54) **Title:** LINERLESS CONTINUOUS AMORPHOUS METAL FILMS

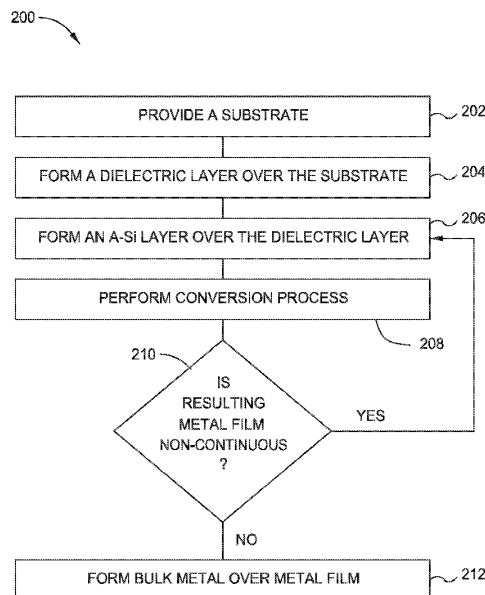


FIG. 2

(57) **Abstract:** Embodiments described herein generally relate to methods of depositing thin films and, more particularly, to depositing metal thin films. The methods herein provide a nucleation free conversion (NFC) approach which involves forming an amorphous silicon layer over the dielectric layer, and performing an NFC process which acts to convert the amorphous silicon layer into a thin metal film. In some embodiments, the NFC process is performed multiple times until the resulting thin metal film is continuous. A bulk metal is formed over the thin metal film.

WO 2020/091961 A1

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Published:

- *with international search report (Art. 21(3))*
- *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments (Rule 48.2(h))*